NX7002AKS

60 V, dual N-channel Trench MOSFET Rev. 1 — 1 March 2012

Product data sheet

Product profile

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

Very fast switching

ESD protection

■ Trench MOSFET technology

1.3 Applications

Relay driver

Low-side load switch

■ High-speed line driver

Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	<u>[1]</u>	-	-	170	mA
Static charac	cteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$		-	3	4.5	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D4 D0
2	G1	gate TR1	6 5 4	D1 D2
3	D2	drain TR2		
4	S2	source TR2	0	$G1 \longrightarrow G2$
5	G2	gate TR2	□1 □2 □3	
6	D1	drain TR1	SOT363 (TSSOP6)	
				S1 S2 017aaa256

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX7002AKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
NX7002AKS	TD%

^{[1] % =} placeholder for manufacturing site code

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor					
V_{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	<u>[1]</u>	-	170	mΑ
		V _{GS} = 10 V; T _{amb} = 100 °C	<u>[1]</u>	-	100	mΑ
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \text{ µs}$		-	680	mΑ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	220	mW
			<u>[1]</u>	-	255	mW
		T _{sp} = 25 °C		-	1060	mW
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	<u>[1]</u>	-	170	mΑ
Per device						
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	330	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

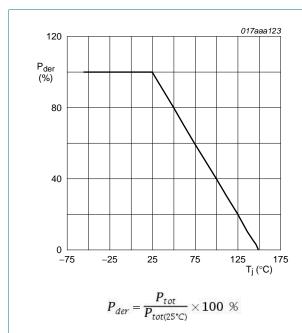
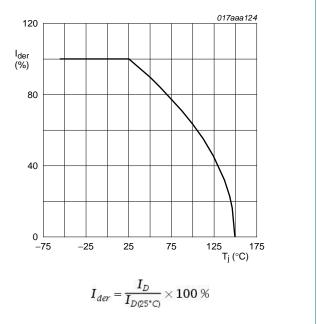
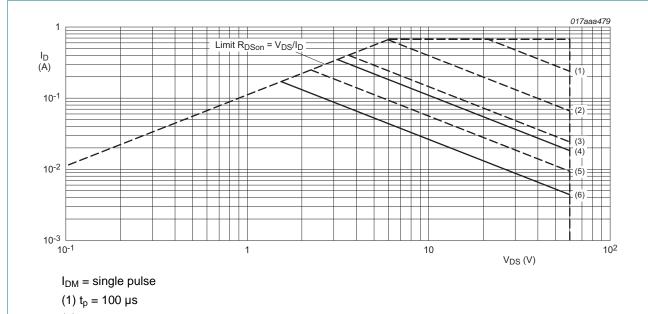


Fig 1. Normalized total power dissipation as a function of junction temperature



ig 2. Normalized continuous drain current as a function of junction temperature

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- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; $T_{sp} = 25 \, ^{\circ}\text{C}$
- (5) $t_p = 100 \text{ ms}$
- (6) DC; $T_{amb} = 25$ °C; drain mounting pad 1 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	500	560	K/W
			[2]	-	450	480	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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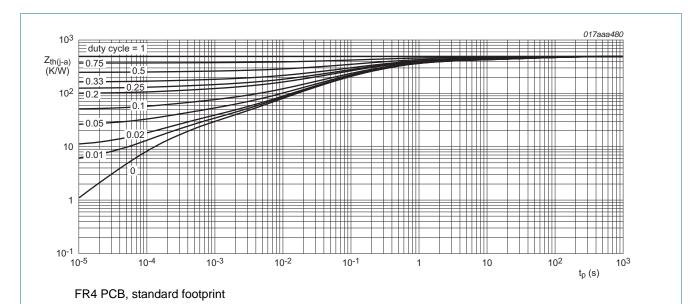


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

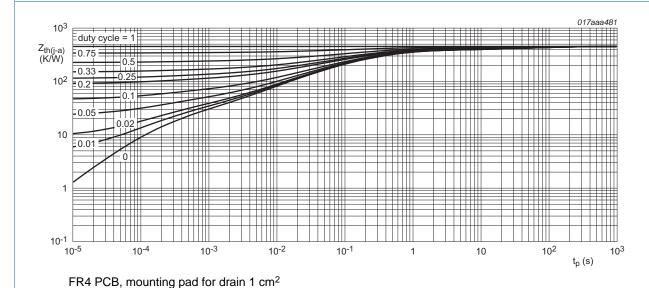


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics			_		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	2	μΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	2	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	0.5	μΑ
		$V_{GS} = 5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R_{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$	-	3	4.5	Ω
	resistance	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 150 \text{ °C}$	-	6.2	9.2	Ω
		$V_{GS} = 5 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$	-	3.7	5.2	Ω
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	230	-	mS
Dynamic o	haracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 200 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.33	0.43	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	$V_{DS} = 10 \text{ V}$; f = 1 MHz; $V_{GS} = 0 \text{ V}$;	-	11	17	pF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}C$	-	3.4	-	pF
C _{rss}	reverse transfer capacitance		-	1.4	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; R_L = 250 Ω ; V_{GS} = 10 V;	-	6	12	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
t _{d(off)}	turn-off delay time		-	20	40	ns
t _f	fall time		-	14	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	0.47	0.7	1.2	V

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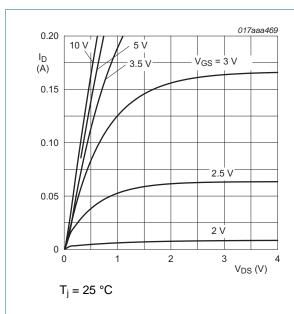


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

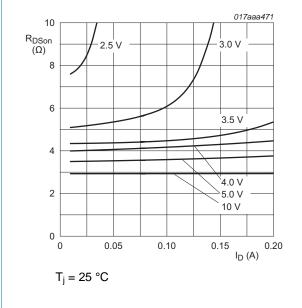
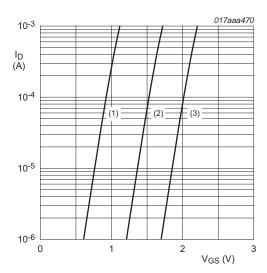


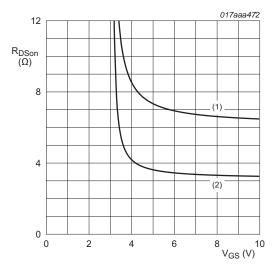
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



 $T_{j} = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Subthreshold drain current as a function of gate-source voltage



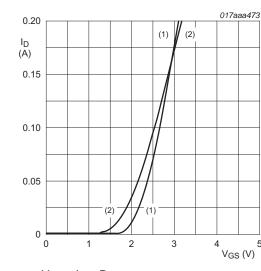
 $I_D = 0.2 A$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

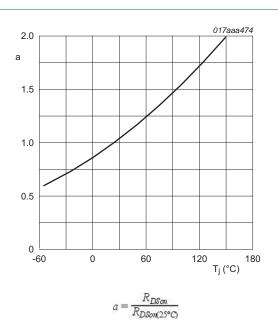
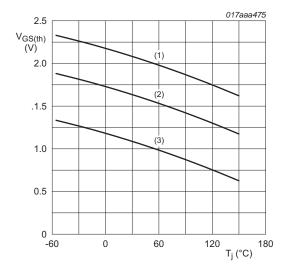


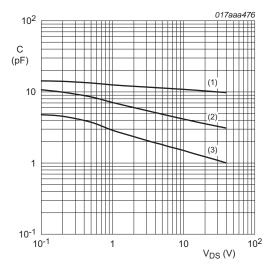
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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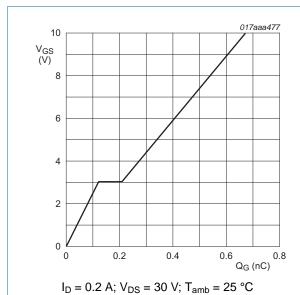
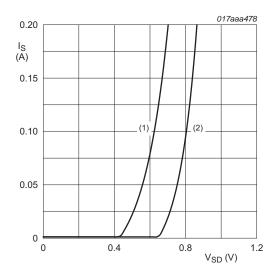


Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

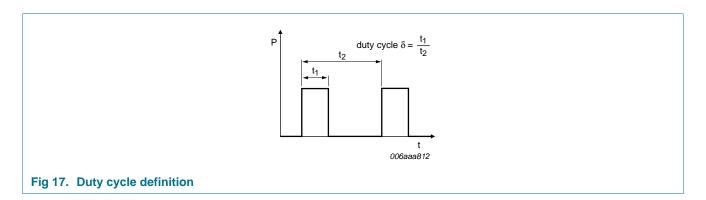
(1) $T_j = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

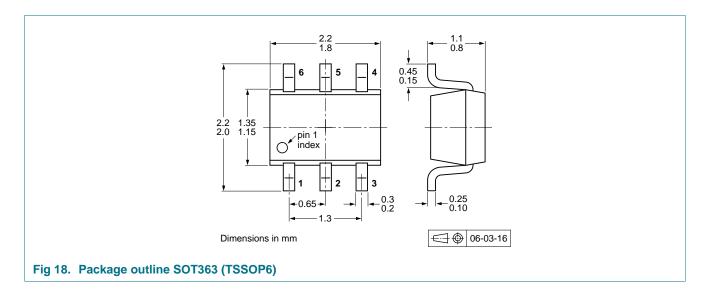
Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information

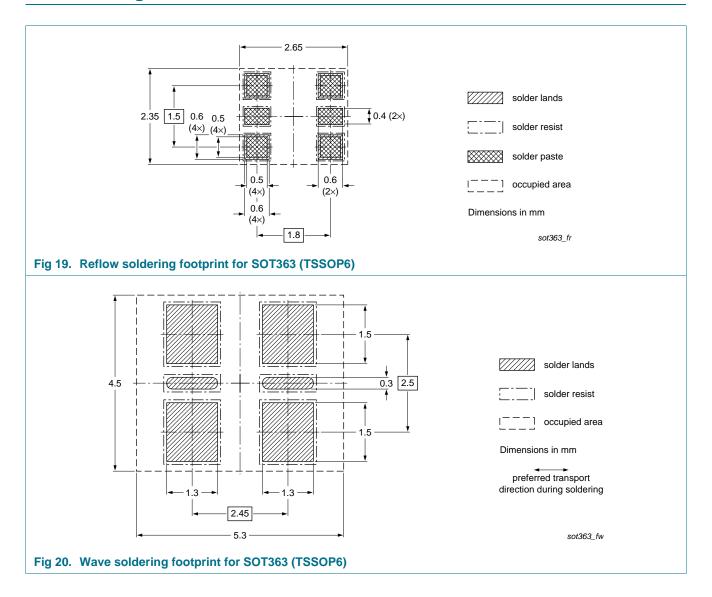


9. Package outline



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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX7002AKS v.1	20120301	Product data sheet	-	-

60 V, dual N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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